Supporting Information

Vapor-fumigation for record efficiency two-dimensional perovskite solar cells with superior stability

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Materials

MAI materials were synthesized according to a method previously reported. Methylammonium solution (24 mL, 33 wt.% in absolute ethanol, Aldrich) was added to a 100 mL 3-neck round-bottom flask; then hydroiodic acid (10 mL, 57 wt.% in water, Aldrich) was slowly dropped into the methylammonium solution at 0 °C. The mixture solution was stirred for 3 hours at 0 °C. Subsequently, the solvents were removed using a rotary evaporator at 60 °C, and the precipitate was obtained. The flaxen powder was dissolved in absolute ethanol; then a certain amount of diethyl ether was added into the solution. The precipitate was filtered by a Buchner funnel. The above steps were repeated once more to obtain powder that was absolutely white. Finally, the pure MAI was dried at 60 °C in a vacuum oven for 24 hours. 2,2',7,7'tetrakis(N,N-di-p-methoxyphenylamine)-9,9'-spirobifluorene (spiro-OMeTAD) was purchased from Yingkou OPV Tech Co., Ltd. PbI₂ (purity > 99.99%) was purchased from Alfa Aesar. The BAI and all of the solvents were purchased from Aldrich and were used without any purification.

Preparation of MA₂PbI₄ film

First, BA₂PbI₄ film was fabricated using the spin-coating method. 402 mg BAI and 462 mg PbI₂ were dissolved in 1 mL γ -butyrolactone and dimethylsulphoxide (7:3. v/v), then stirred at 60 °C overnight. The solution was filtered through a 0.22 µm filter element then spin-coated on the substrate using the anti-solvent method by a two-step spin-coating process at 1000 and 4000 rpm for 15 and 45 s, respectively. The 2.5 cm × 2.5 cm sample was treated with 200 µL chlorobenzene when the second spincoating step had 20 s remaining. The yellowish-orange BA₂PbI₄ film (Fig. S1, left) was obtained. Then, the BA₂PbI₄ film was placed on a hot-plate at 300 °C for 30 min, and the PbI₂ film formed on the substrate (Fig. S1, middle).After cooling to room temperature, the PbI₂ sample was transferred onto a layer of MAI powder, heated to 150 °C and maintained at this temperature for 20 min. Finally, the brownish black MA₂PbI₄ thin film (Fig. S1, right) was obtained.

Calculation

In our calculations, the crystal structural parameter and electronic structure are calculated based on the plane wave method in the framework of density-functional theory (DFT) as implemented in the Vienna ab initio simulation package (VASP) code. The projector augmented wave (PAW) pseudopotentials are used to describe the interaction between ion-cores and valence electrons. The generalized gradient approximation (GGA) with the Perdew Burke Ernzerhof (PBE) functional is used for the exchange-correlation effects, and an energy cutoff of 450 eV is set for the plane wave function's expansion. For the Brillouin zone intergration, a Γ -centered 3 × 3 × 1 and 3 × 3 × 2 Monkhorst-Pack k-point sampling meshes are used for monolayer structure and bulk structure, resectively. The spin-orbit coupling was also considered in the electronic structure calculations and the van der Waals (vdW) interaction between 2D layers are described by the DFT-D3 correction. The lattice parameter and atomic positions of the all structures are relaxed untill the total energy changes were less than 1.0×10^{-5} eV. Periodic boundary condition is applied along the in plane direction and a vacuum spacing >15 Å is set along the direction perpendicular to the sheet plane to avoid the interaction between period cells.

Device fabrication

Glass/FTO substrates were cleaned with acetone, isopropyl alcohol and deionized water in an ultrasonic bath for 30 min, respectively, and then dried by flowing nitrogen gas. The TiO₂ electron transport layers of ~ 60 nm-thick were deposited on FTO substrates using a chemical bath according to previous report. The FTO/TiO₂ substrates were exposed to ultraviolet light and ozone for 15 min, and then the perovskite absorbers were deposited. The 90 mg mL⁻¹ spiro-OMeTAD chlorobenzene solution, mixed with dopants of 36 μ L 4-tert-butylpyridine and 22 μ L lithium bis(trifluoromethylsulfonyl) imide at 520 mg mL⁻¹ in acetonitrile, was spin-coated onto the perovskite films at 3000 rpm for 30 s. Finally, 100-nm-thick gold layers were deposited using a thermal evaporator.

Characterization

The *J-V* curves were performed using a Keithley 2400 SourceMeter under ambient temperature and air conditions. The light source was a 450 W Xenon lamp (Oriel

solar simulator) equipped with a SchottK113 Tempax sunlight filter (Praezisions Glas & OptikGmbH) to match the emission spectrum of the lamp to the AM1.5G standard. Before each measurement, the illumination intensity was 100 mWcm⁻² calibrated by an NREL-traceable KG5-filtered silicon reference cell. The scan rate was 0.1 V s⁻¹, the scan step was 0.02 V, and the scan delay time was 10 ms. A non-reflective black mask with an aperture area of 0.09052 cm² was covered part of the active area (0.1134 cm^2) to avoid light scattering through the sides during the measurement. The aperture area was determined by the MICRO VUE sol 161 instrument. The EQE was acquired using a Crowntech QTest Station 2000ADI system. The light source was a 300 W xenon lamp, and the monochromatic light intensity for the EQE measurement was calibrated with a reference silicon photodiode. GIWAXS measurements were performed in the D-line at the Cornell High Energy Synchrotron Source (CHESS). The x-rays wavelength was 1.166 Å with a bandwidth $\Delta\lambda\lambda$ of 1.5%. The scattering 10 signal was collected using a Pilatus 200K detector. The incident angle of the x-ray beam was at 0.25°, and the integration time was 1 s. Steady-state PL (excitation at 532 nm) measurements were carried out using an Edinburgh Instruments Ltd (FLS980). The TRPL spectra were acquired on an Edinburgh Instruments FLS980 fluorescence spectrometer with the time-correlated single-photon counting method. SEM images were obtained by a field emission scanning electron microscope (SU8020) with an accelerating voltage of 3 keV. XRD patterns were acquired on a SmartLab x-ray diffraction system. The UV-Vis spectra were acquired by a PerkinElmer 10 UV-Lambda 950 instrument. XPS data were measured on a Thermo Fisher Scientific (K-Alpha system) using Al K α as the exciting x-ray source at a pressure of 1×10^{-8} Pa.



Fig. S1. Photograph of BA_2PbI_4 , PbI_2 , and MA_2PbI_4 films.



Fig. S2. Decomposition analysis of BA₂PbI₄ and MA₂PbI₄ powder. TGA was performed from room temperature to 350 °C under active nitrogen gas flow. There is weight loss observed below 160 °C caused by the removal of other impurities adsorbed on the BA₂PbI₄ powder. When the temperature exceeded 160 °C, the TGA curve sharp declined, indicating that the BA₂PbI₄ started decomposition into BA, HI and PbI₂. As the temperature continuously increased, BA and HI completely sublimated. This decomposition ended at 280 °C, and the weight of the residual is approximately 56% of its initial total value, which is very close to the mass proportion of PbI₂ in BA₂PbI₄, meaning that PbI₂ template is successfully generated by BA₂PbI₄ decomposition. In addition, TGA of MA₂PbI₄ powder was measured. When it is heated to beyond 132 °C, the TGA curve drops sharply, indicating that the MA₂PbI₄ starts to decompose into MA, HI and PbI₂. When the temperature overs 269 °C, the net mass hits a plateau, indicating that the volatile MA and HI are completely gone. It is clear that the thermal decomposition of MA₂PbI₄ starts at 132 °C, lower than that of BA₂PbI₄.



Fig. S3 SEM images of (a) PbI_2 film fabricated by spin-coating, and (b) PbI_2 template film. Corresponding top-view SEM images of (c) 3D perovskite film, and (d) 2D perovskite film. (e) XRD patterns of films based on various PbI_2 films.



Fig. S4. GIWAXS images for (a) BA₂PbI₄ and (b) MA₂PbI₄.



Fig. S5. The band gap (E_g) of BA_2PbI_4 and MA_2PbI_4 films established from the corresponding absorbance spectra.



Fig. S6. Estimated exciton binding energy by absorption spectra. The 2D perovskites show a typical exciton peak and a step-like band-to-band absorption. The exciton binding energy of BA_2PbI_4 and MA_2PbI_4 are 502 meV and 153 meV, respectively.



Fig. S7. Dark *I-V* curves of the MAPbI₃ devices.



Fig. S8. XRD spectra of MAPbI₃ stored at 70% humidity for different time.



Fig. S9. Certificated results of 2D MA₂PbI₄ PSC from the National Institute of Metrology (NIM) of China. The certificated efficiency is 16.6% with $J_{sc} = 20.77$ mA cm⁻², $V_{oc} = 1.08$ V and FF = 73.9%. A mask area of 9.052 mm² has been used when certification.



Fig. S10. *J-V* characterizations of BA_2PbI_4 PSCs scanned at the reverse and forward directions.



Fig. S11. EQE and absorbance curves of MA_2PbI_4 . EQE curve of a PSC based on MA_2PbI_4 absorber and absorbance spectra of 2D MA_2PbI_4 film. Both edge lines cut off at ca. 800 nm. The EQE shows a fast decline from 650 to 750 nm, which indicates weak absorption in this range due to the thinness of the 179 nm-thick MA_2PbI_4 absorber (Fig. 4b).

BA ₂ PI ₄			MA ₂ PbI ₄		
Triclinic	a	8.46	Triclinic	a	8.57
	b	8.69		b	8.71
	c	28.62		c	19.31
	α	83.91		α	101.38
	β	90.77		β	100.96
	γ	90.12		γ	91.65
Layer spacing	d	14.2	Layer spacing	d	9.2

Table S1. The optimized lattice parameters of BA_2PbI_4 and MA_2PbI_4 .

Table S2. The electrical conductivity of BA_2PbI_4 and MA_2PbI_4 films.

Device	$J_{\rm sc}$ (mA cm ⁻²)	$V_{\rm oc}$ (V)	FF	PCE (%)
1	19.17	1.00	0.70	13.42
2	19.65	0.98	0.71	13.67
3	21.05	0.96	0.71	14.35
4	20.68	0.98	0.75	15.20
5	19.17	0.96	0.75	13.80
6	20.49	0.96	0.75	14.75
7	20.50	0.98	0.76	15.27
8	19.75	0.98	0.76	14.71
9	21.66	0.98	0.76	16.13
10	21.18	0.98	0.76	15.77
11	18.02	1.00	0.77	13.88
12	19.33	0.96	0.77	14.29
13	19.31	0.98	0.78	14.76
14	21.00	1.06	0.76	16.91
15	21.40	0.96	0.60	12.33
16	19.79	0.90	0.61	10.86
17	20.53	0.90	0.61	11.27
18	22.07	0.96	0.62	13.14
19	20.35	0.96	0.62	12.11
20	21.34	0.96	0.62	12.70
21	20.44	0.96	0.62	12.17
22	22.83	0.94	0.63	13.52
23	22.71	0.92	0.63	13.16
24	19.51	0.96	0.65	12.17
25	23.12	0.92	0.65	13.83
26	23.22	0.90	0.66	13.79
27	22.47	0.90	0.66	13.35
28	20.68	0.90	0.66	12.28
29	22.65	0.92	0.68	14.17

Table S3. The parameters of MA_2PbI_4 solar cells.

30	22.39	0.92	0.68	14.01
Average	20.88 ± 1.36	0.98 ± 0.04	0.73 ± 0.06	14.18 ± 1.40

References

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